

In the Abstract:

Please **replace** the paragraph at **page 23, lines 2 to 9**, with a replacement paragraph amended as follows:

There is provided a method of fabricating semiconductor devices that allows ion implantation to be performed at high temperature with ions accelerated with high energy to help to introduce dopant in a semiconductor ~~substrate (1, 101),~~ substrate, in particular a SiC semiconductor substrate, at a selected region to sufficient depth. To achieve this the method includes the steps of: providing the semiconductor substrate ~~[(1, 101)]~~ at a surface thereof with a mask layer including a polyimide resin ~~film (2),~~ film, or a SiO₂ film ~~(107a, 107b)~~ and a thin metal ~~film (105),~~ film; and introducing dopant ions.

[REMARKS FOLLOW ON NEXT PAGE]